

TO-92 Plastic-Encapsulate Transistors

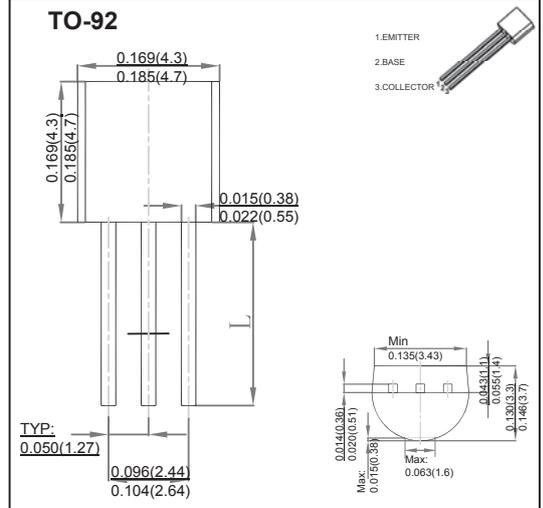
FEATURES

- High Breakdown Voltage
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|-----------------|---|------------|-------|
| V_{CBO} | Collector-Base Voltage | 400 | V |
| V_{CEO} | Collector-Emitter Voltage | 400 | V |
| V_{EBO} | Emitter-Base Voltage | 6 | V |
| I_C | Collector Current -Continuous | 0.3 | A |
| P_D | Collector Power Dissipation | 625 | mW |
| $R_{\theta JA}$ | Thermal Resistance from Junction to Ambient | 200 | °C /W |
| T_j | Junction Temperature | 150 | °C |
| T_{stg} | Storage Temperature | -55 ~ +150 | °C |

ELECTRICAL CHARACTERISTICS $T_a = 25^\circ\text{C}$ unless otherwise specified

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|--------------------------------------|--------------------|--|-----|-----|------|---------------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C = 0.1\text{mA}, I_E = 0$ | 400 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}^*$ | $I_C = 1\text{mA}, I_B = 0$ | 400 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E = 0.1\text{mA}, I_C = 0$ | 6 | | | V |
| Collector cut-off current | I_{CBO} | $V_{CB} = 400\text{V}, I_E = 0$ | | | 0.1 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = 4\text{V}, I_C = 0$ | | | 0.1 | μA |
| DC current gain | $h_{FE(1)}^*$ | $V_{CE} = 10\text{V}, I_C = 1\text{mA}$ | 40 | | | |
| | $h_{FE(2)}^*$ | $V_{CE} = 10\text{V}, I_C = 10\text{mA}$ | 50 | | 200 | |
| | $h_{FE(3)}^*$ | $V_{CE} = 10\text{V}, I_C = 50\text{mA}$ | 45 | | | |
| | $h_{FE(4)}^*$ | $V_{CE} = 10\text{V}, I_C = 100\text{mA}$ | 40 | | | |
| Collector-emitter saturation voltage | $V_{CE(sat)(1)}^*$ | $I_C = 1\text{mA}, I_B = 0.1\text{mA}$ | | | 0.4 | V |
| | $V_{CE(sat)(2)}^*$ | $I_C = 10\text{mA}, I_B = 1\text{mA}$ | | | 0.5 | |
| | $V_{CE(sat)(3)}^*$ | $I_C = 50\text{mA}, I_B = 5\text{mA}$ | | | 0.75 | |
| Base-emitter saturation voltage | $V_{BE(sat)}^*$ | $I_C = 10\text{mA}, I_B = 1\text{mA}$ | | | 0.75 | V |
| Collector output capacitance | C_{ob} | $V_{CB} = 20\text{V}, I_E = 0, f = 1\text{MHz}$ | | | 7 | pF |
| Emitter input capacitance | C_{ib} | $V_{EB} = 0.5\text{V}, I_C = 0, f = 1\text{MHz}$ | | | 130 | pF |

*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycles $\leq 2.0\%$.